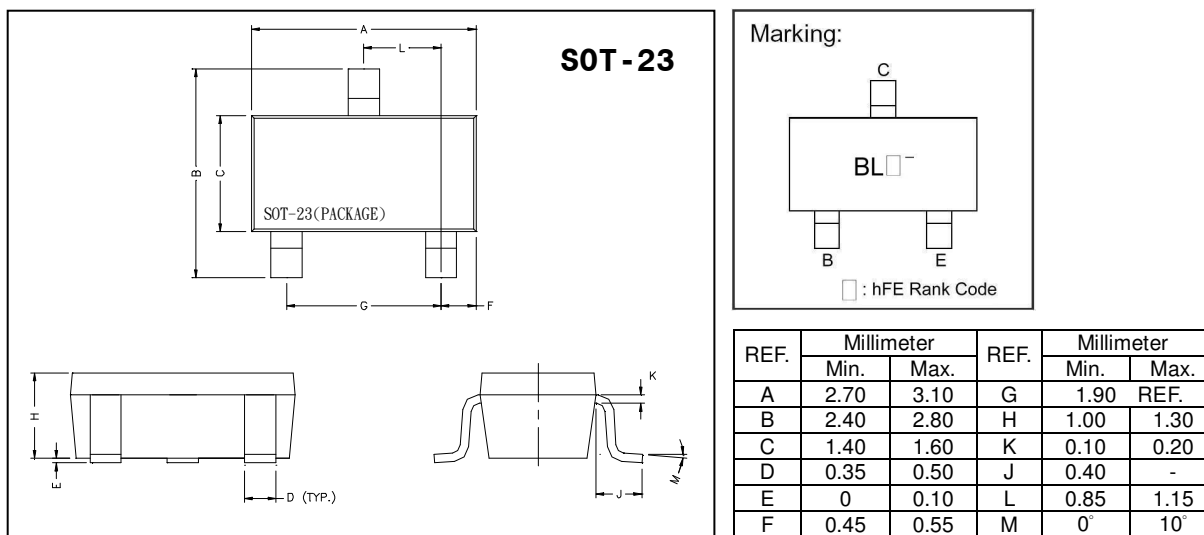


GMBT8550L PNP EPITAXIAL TRANSISTOR

Description

The GMBT8550L(large current) is designed for general purpose amplifier applications.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CBO}	-40	V
Collector to Emitter Voltage	V _{CEO}	-25	V
Emitter to Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	1.5	A
Total Power Dissipation	P _D	250	mW

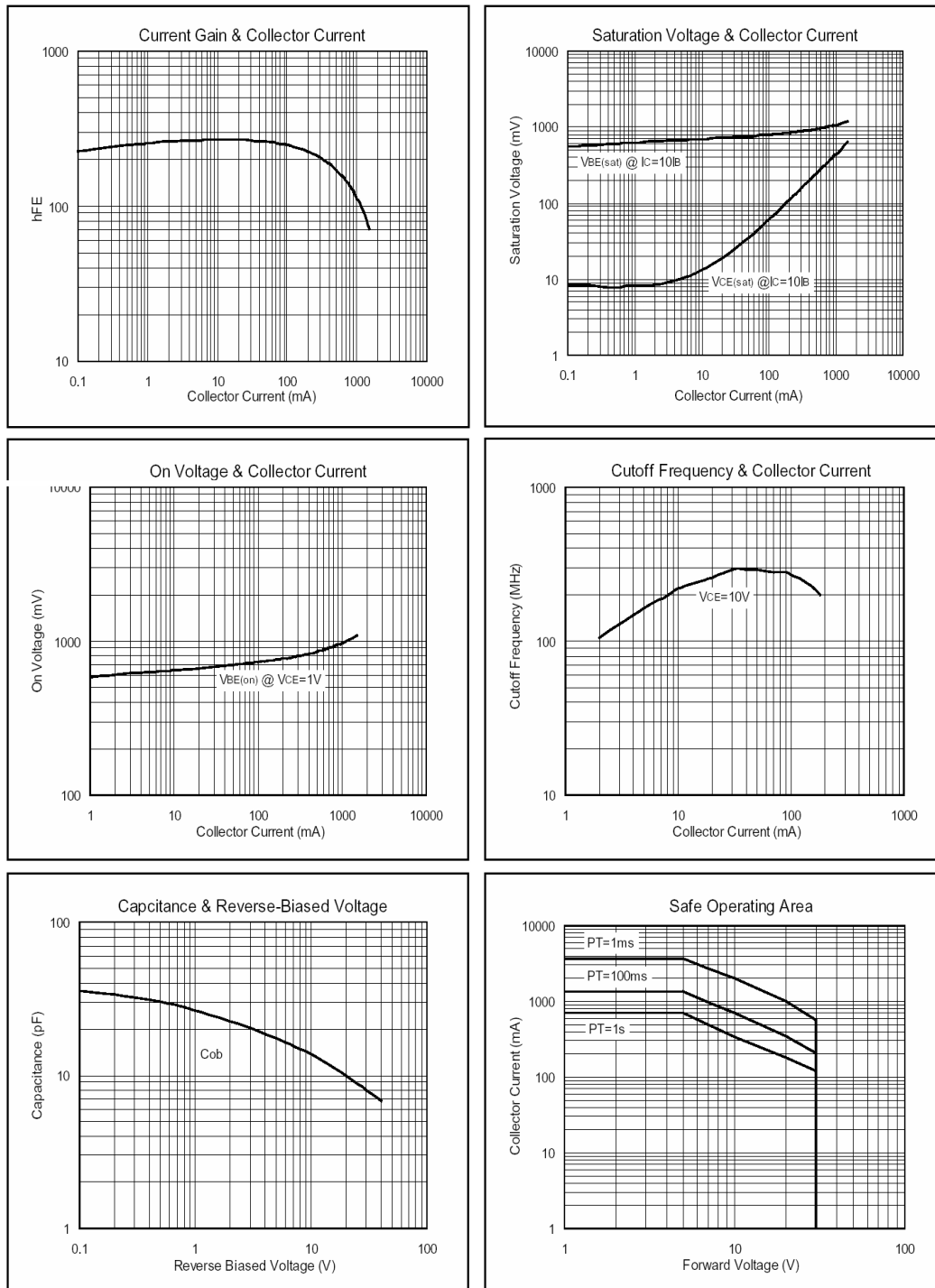
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
B _V C _{BO}	-40	-	-	V	I _C =-100uA
B _V C _{EO}	-25	-	-	V	I _C =-2mA
B _V E _{BO}	-6	-	-	V	I _E =-100uA
I _C B _O	-	-	-100	nA	V _{CB} =-35V, I _E =0
I _E B _O	-	-	-100	nA	V _{EB} =-6V, I _C =0
V _{CE} (sat)	-	-	-0.5	V	I _C =-800mA, I _B =-80mA
V _{BE} (sat)	-	-	-1.2	V	I _C =-800mA, I _B =-80mA
V _{BE} (on)	-	-	-1	V	V _{CE} =-1V, I _C =-10mA
h _{FE}	45	-	-		V _{CE} =-1V, I _C =-5mA
h _{FE}	120	-	500		V _{CE} =-1V, I _C =-100mA
h _{FE}	40	-	-		V _{CE} =-1V, I _C =-800mA
f _T	100	-	-	MHz	V _{CE} =-10V, I _C =-20mA, f=100MHz
C _{ob}	-	-	10	pF	V _{CB} =-10V, f=1MHz

Classification Of hFE

Rank	BLC	BLD	BLE
hFE	120 - 200	160 - 300	250 - 500

Characteristics Curve



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